inter_{sil}

DATASHEET

HS-6664RH-T

Radiation Hardened 8K x 8 CMOS PROM

Intersil's Satellite Applications Flow[™] (SAF) devices are fully tested and guaranteed to 100kRAD total dose. These QML Class T devices are processed to a standard flow intended to meet the cost and shorter lead-time needs of large volume satellite manufacturers, while maintaining a high level of reliability.

The Intersil HS-6664RH-T is a radiation hardened 64K CMOS PROM, organized in an 8K word by 8-bit format. The chip is manufactured using a radiation hardened CMOS process, and utilizes synchronous circuit design techniques to achieve high speed performance with very low power dissipation.

On-chip address latches are provided, allowing easy interfacing with microprocessors that use a multiplexed address/data bus structure. The output enable control (\overline{G}) simplifies system interfacing by allowing output data bus control in addition to the chip enable control (\overline{E}). All bits are manufactured storing a logical "0" and can be selectively programmed for a logical "1" at any bit location.

Specifications

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the HS-666s4RH-T are contained in SMD 5962-95626. For more information, visit our website at: www.intersil.com/

Intersil's Quality Management Plan (QM Plan), listing all Class T screening operations, is also available on our website.

www.intersil.com/

Ordering Information

ORDERING INFORMATION	PART NUMBER	TEMP. RANGE (^o C)
5962R9562601TXC	HS1-6664RH-T	-55 to 125
HS1-6664RH/Proto	HS1-6664RH/Proto	-55 to 125
5962R9562601TYC	HS9-6664RH-T	-55 to 125
HS9-6664RH/Proto	HS9-6664RH/Proto	-55 to 125

NOTE: Minimum order quantity for -T is 150 units through distribution, or 450 units direct.

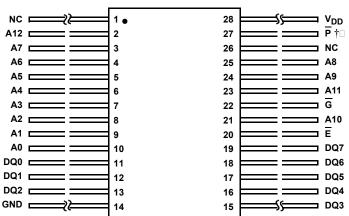
Features

- QML Class T, Per MIL-PRF-38535
- Radiation Performance
 - Gamma Dose (γ) 1 x 10⁵ RAD(Si)
 - No Latch-Up, SEU LET >100MeV/mg/cm²
- Transient Output Upset >5 x 10⁸ RAD (Si)/s
- Fast Access Time 35ns (Typical)
- Single 5V Power Supply, Synchronous Operation
- Single Pulse 10V Field Programmable NiCr Fuses
- On-Chip Address Latches, Three-State Outputs
- Low Standby Current <500μA (Pre-Rad)
- Low Operating Current <15mA/MHz

Pinouts

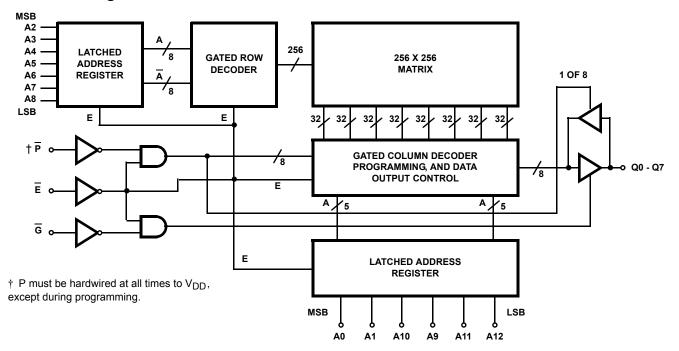
HS1-6664RH-T (SBDIP), CDIP2-T28 TOP VIEW			
NC 1 A12 2 A7 3 A6 4 A5 5 A4 6 A3 7 A2 8 A1 9 A0 10 DQ1 11 DQ1 12 DQ2 13 GND 14		28 V _{DD} 27 P † 26 NC 25 A8 24 A9 23 A11 22 G 21 A10 20 E 19 DQ7 18 DQ5 16 DQ4 15 DQ3	

HS9-6664RH-T (FLATPACK), CDFP3-F28 TOP VIEW



 $\dagger\,\overline{\mathsf{P}}$ must be hardwired at all times to $\mathsf{V}_{DD},$ except during programming.

Functional Diagram



TRUTH TABLE				
E	G	MODE		
0	0	Enabled		
0	1	Output Disabled		
1	Х	Disabled		

Timing Waveform

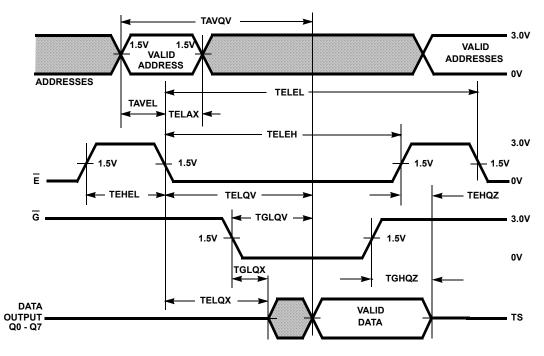


FIGURE 1. READ CYCLE

Die Characteristics

DIE DIMENSIONS:

(6883μm x 7798μm x 483μm ±25.4μm) 271 x 307 x 19mils ±1mil

METALLIZATION:

MI: $6k\dot{A} \pm 1k\dot{A}$ Si/Al/Cu $2k\dot{A} \pm 500\dot{A}$ TiW M2: $10k\dot{A} \pm 2k\dot{A}$ Si/Al/Cu

SUBSTRATE POTENTIAL:

 V_{DD}

BACKSIDE FINISH:

Silicon

Metallization Mask Layout

PASSIVATION:

Type: Silox (S_iO₂) Thickness: 8kÅ ±1kÅ

WORST CASE CURRENT DENSITY:

< 2.0e5 A/cm²

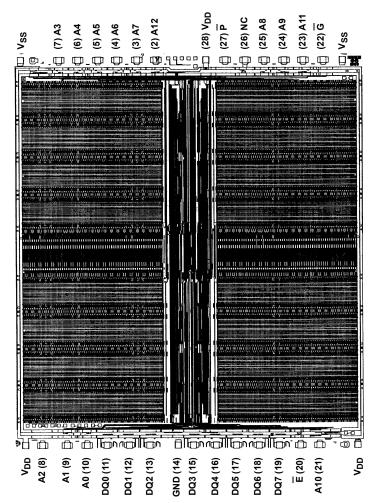
TRANSISTOR COUNT:

110, 874, (27,719 Gates)

PROCESS:

AVLSI

HS-6664RH-T



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